Title: DRAM Cell Having MOS Capacitor and Method

for Manufacturing the Same

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FIG. 1 (PRIOR ART)

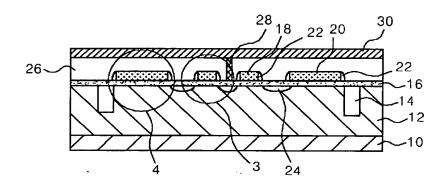
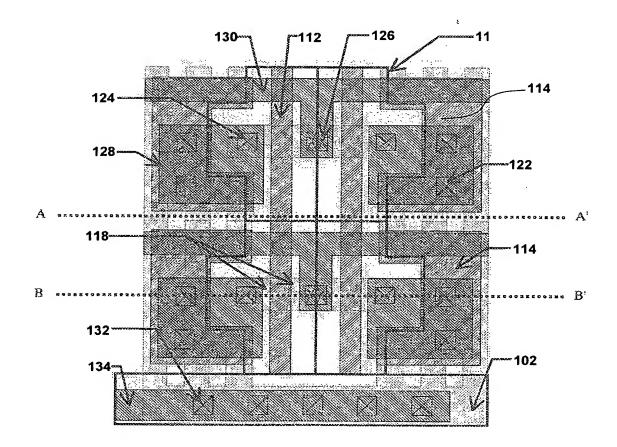


FIG. 2



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FIG. 3

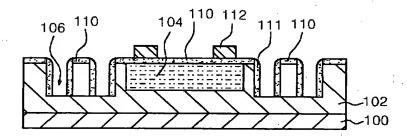


FIG. 4

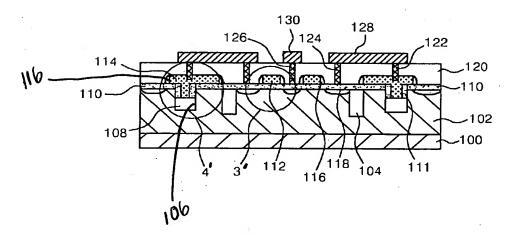
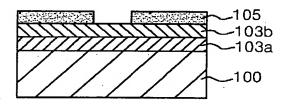
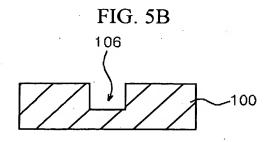


FIG. 5A



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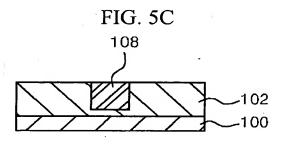


FIG. 5D

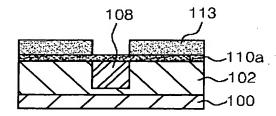
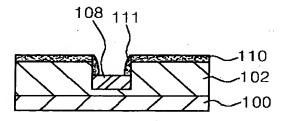


FIG. 5E



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FIG. 5F

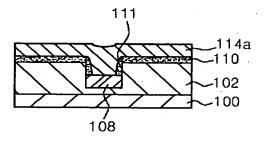


FIG. 5G

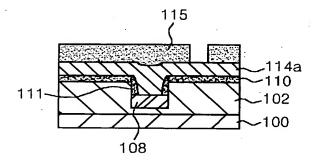
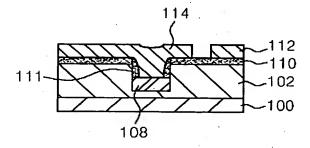


FIG. 5H



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FIG. 5I

